

MICROWAVE POWER GAN HEMT

TGI5867-50L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED HEMT
- ·HIGH POWER

Pout= 47.0dBm at Pin= 39.0dBm

·HIGH GAIN

GL= 13.5dB at 5.85GHz to 6.75GHz

-LOW INTERMODULATION DISTORTION

IM3(Min.)= -40dBc at Po=32.0dBm Single Carrier Level

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V	dBm	46.0	47.0	_
Drain Current	IDS1	IDSset= 3.0A f= 5.85 to 6.75GHz @Pin= 39dBm	А	_	5.4	6.3
Power Added Efficiency	ηadd		%	_	33	_
Linear Gain	GL	@Pin= 20dBm	dB	12.5	13.5	_
Gain flatness	ΔG		dB	_	_	±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test	dBc	-40	_	_
Drain Current	IDS2	Po= 32.0dBm, Δf= 5MHz (Single Carrier Level)	А		3.5	4.5
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – Pout) X Rth(c-c)	°C	_	130	150

Recommended Gate Resistance(Rg): 60 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 5.0A	S	_	4.5	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 23mA	V	-2.6	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А	_	15	_
Gate-Source Breakdown Voltage	VGSO	IGS= -10mA	٧	-10	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.4	1.6

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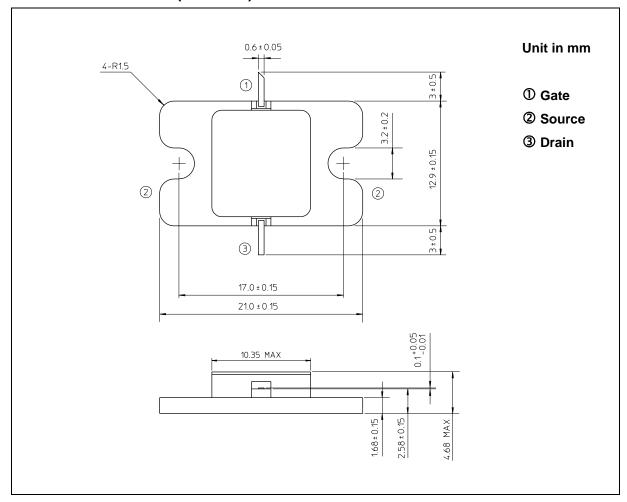
- MICROWAVE SEMICONDUCTOR TECHNICAL DATA



ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	15
Total Power Dissipation (Tc= 25 °C)	PT	W	140
Channel Temperature	Tch	°C	250
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA04A)

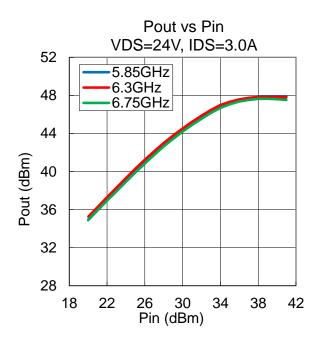


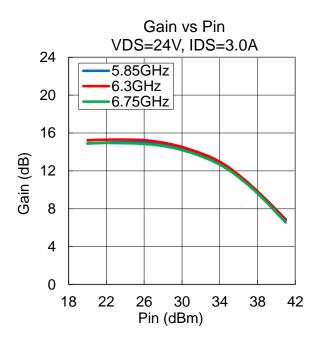
HANDLING PRECAUTIONS FOR PACKAGE MODEL

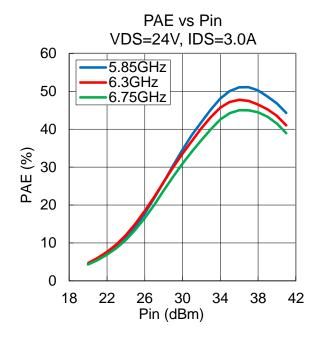
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

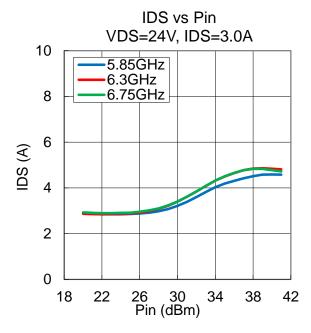
·Pout, Gain, PAE, IDS vs. Pin

VDS= 24 V, IDSset= 3.0 A, f= 5.85, 6.3, 6.75 GHz, Ta= +25 °C



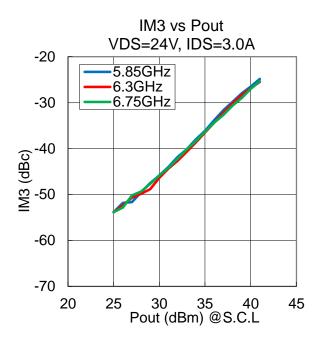


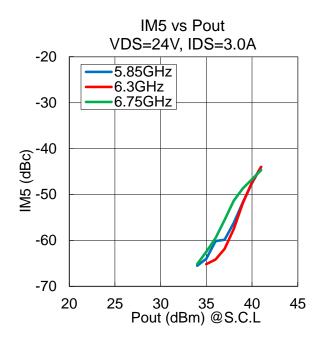




·IM3, IM5 vs. Pout

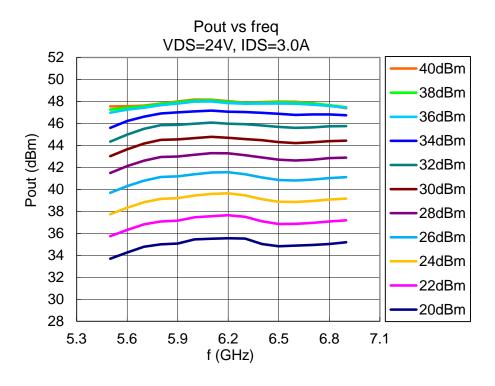
VDS= 24 V, IDSset= 3.0 A, f= 5.85, 6.3, 6.75 GHz, Δ f= 5 MHz , Ta= +25 °C





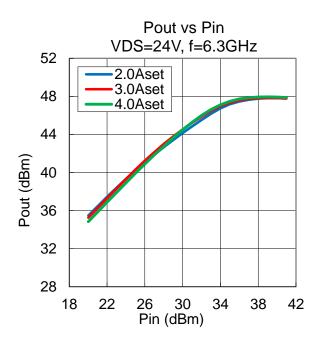
·Pout vs. Frequency

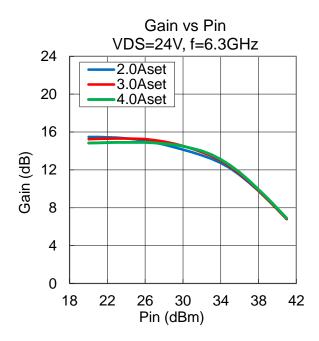
VDS= 24 V, IDSset= 3.0 A, Ta= +25 °C

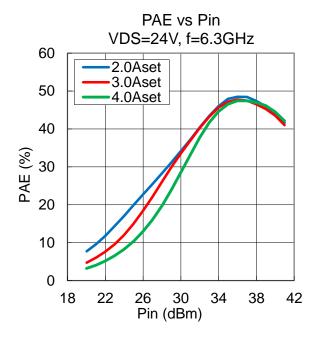


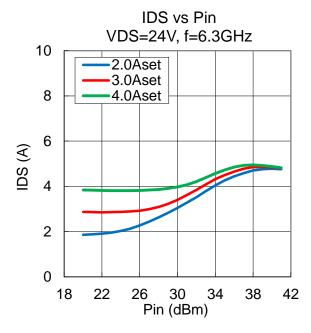
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 24 V, IDSset= 2.0, 3.0, 4.0 A, f= 6.3 GHz, Ta= +25 °C





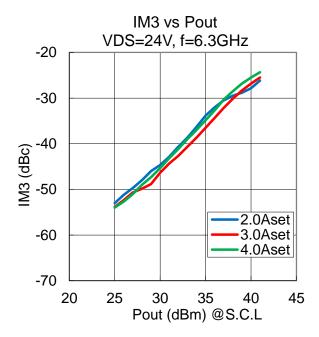


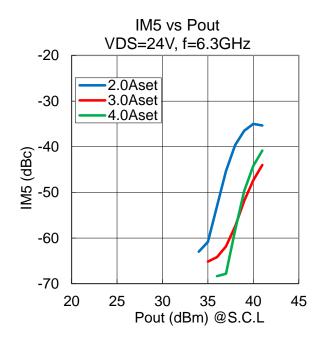




·IM3, IM5 vs. Pout vs. IDSset

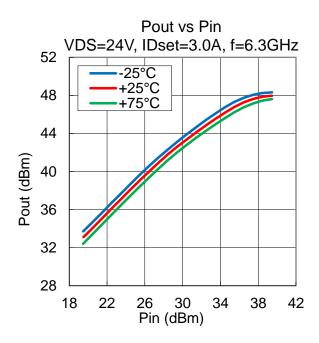
VDS= 24 V, IDSset= 2.0, 3.0, 4.0 A, f= 6.3 GHz, Δ f= 5 MHz, Ta= +25 °C

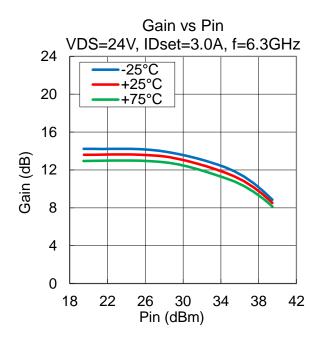


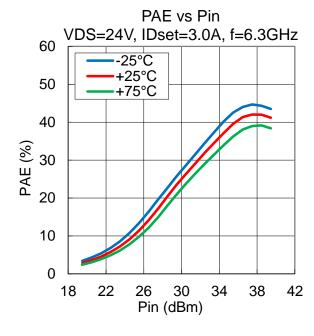


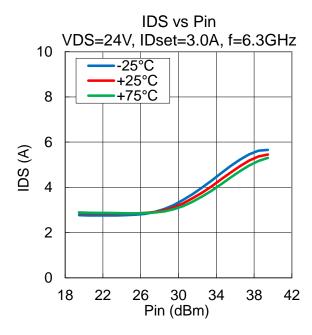
·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 24 V, IDSset= 3.0 A, f= 6.3 GHz, Ta= -25, +25, +75 °C



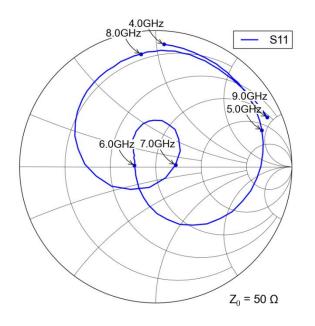


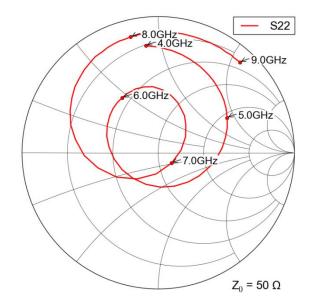


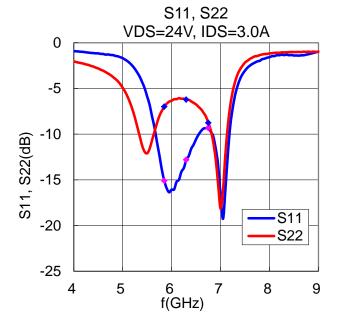


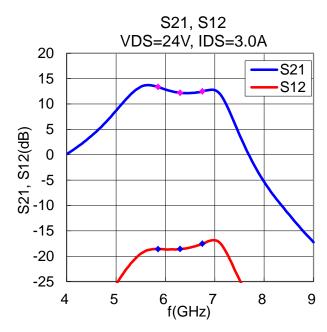
-S-Parameters

VDS= 24 V, IDSset= 3.0 A, f= 4.0 to 9.0 GHz, Ta= +25 °C











MICROWAVE POWER GAN HEMT TGI5867-50L

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